

Important notice

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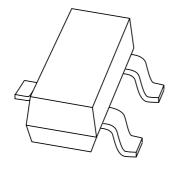
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PMBD6050 High-speed diode

Product data sheet Supersedes data of 1999 May 11 2004 Jan 14



High-speed diode

PMBD6050

FEATURES

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 70 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

APPLICATIONS

• High-speed switching in thick and thin-film circuits.

DESCRIPTION

The PMBD6050 is a high-speed switching diode fabricated in planar technology, and encapsulated in a small SOT23 plastic SMD package.

MARKING

TYPE NUMBER	MARKING CODE(1)	
PMBD6050	*5A	

Note

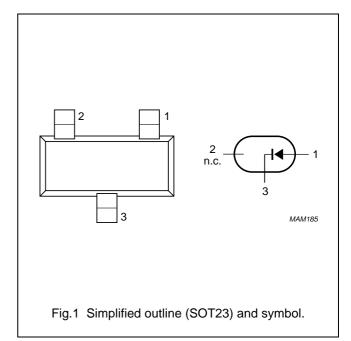
1. * = p : Made in Hong Kong.

* = t : Made in Malaysia.

* = W : Made in China.

PINNING

PIN	DESCRIPTION
1	anode
2	not connected
3	cathode



ORDERING INFORMATION

TYPE	PACKAGE			
NUMBER	NAME	DESCRIPTION	VERSION	
PMBD6050	_	plastic surface mounted package; 3 leads	SOT23	

High-speed diode

PMBD6050

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage		_	85	V
V_R	continuous reverse voltage		-	70	V
I _F	continuous forward current	note 1; see Fig.2	_	215	mA
I _{FRM}	repetitive peak forward current		-	500	mA
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4			
		t = 1 μs	_	4	Α
		t = 1 ms	_	1	Α
		t = 1 s	_	0.5	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	-	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

High-speed diode

PMBD6050

ELECTRICAL CHARACTERISTICS

 T_{j} = 25 $^{\circ}C$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V _F	forward voltage	see Fig.3		
		I _F = 1 mA	715	mV
		I _F = 10 mA	855	mV
		I _F = 50 mA	1	V
		I _F = 150 mA	1.25	V
I_R	reverse current	see Fig.5		
		V _R = 50 V	100	nA
		V _R = 50 V; T _j = 150 °C	50	μΑ
C_d	diode capacitance	$f = 1 \text{ MHz}$; $V_R = 0$; see Fig.6	1.5	pF
t _{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.7	4	ns
V _{fr}	forward recovery voltage	when switched from $I_F = 10$ mA; $t_r = 20$ ns; see Fig.8	1.75	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-tp)}	thermal resistance from junction to tie-point		330	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

Note

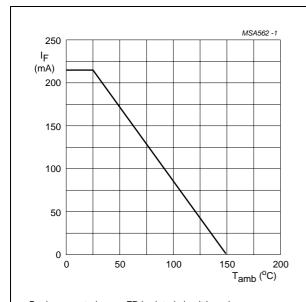
1. Device mounted on an FR4 printed-circuit board.

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High-speed diode

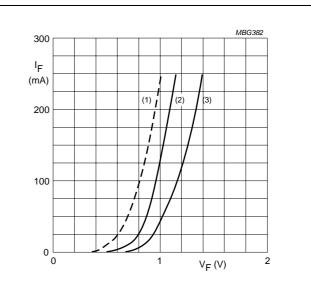
PMBD6050

GRAPHICAL DATA



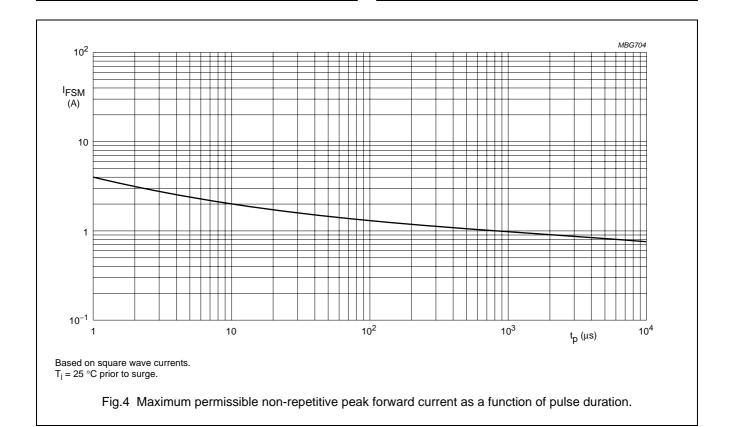
Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



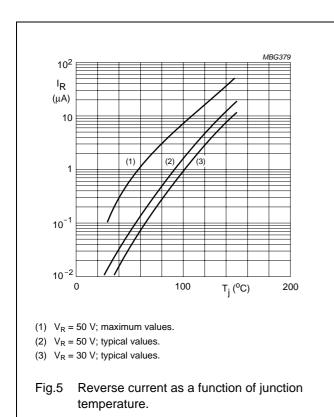
- (1) $T_i = 150 \,^{\circ}\text{C}$; typical values.
- (2) $T_j = 25$ °C; typical values.
- (3) $T_j = 25$ °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



High-speed diode

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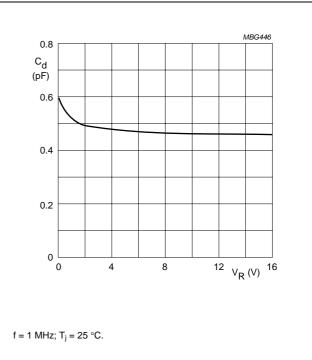
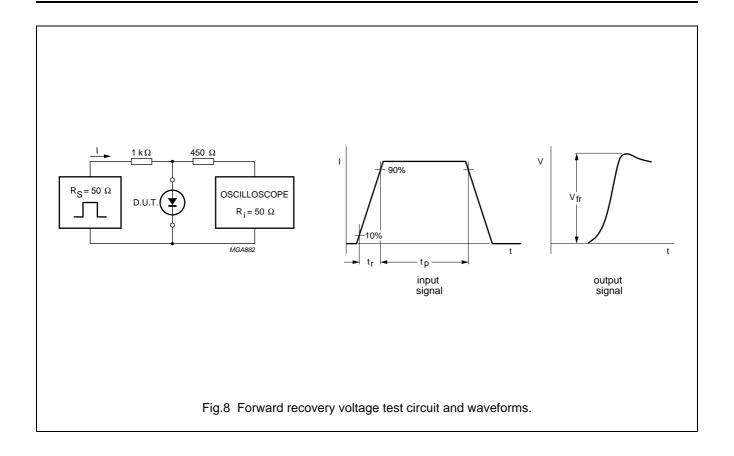


Fig.6 Diode capacitance as a function of reverse voltage; typical values.

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High-speed diode

PMBD6050



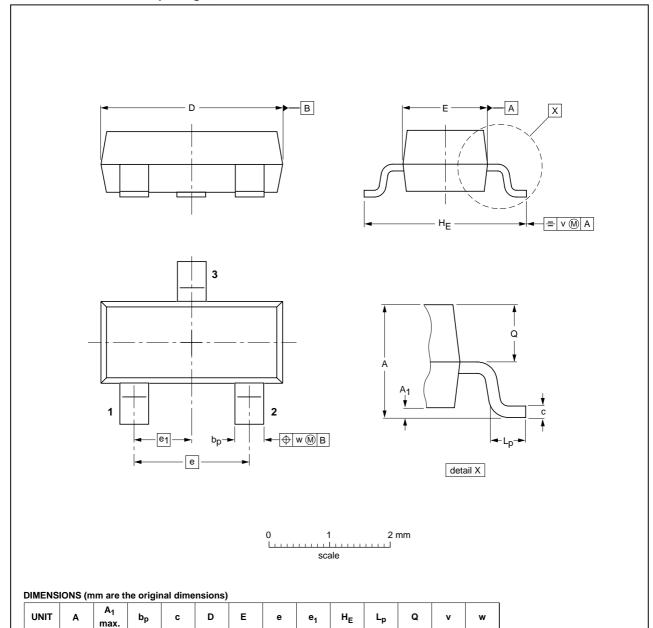
High-speed diode

PMBD6050

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOTOS		TO 226AB			-04-11-04

0.45

0.55

0.1

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max

0.38

0.9

High-speed diode

PMBD6050

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com
For sales offices addresses send e-mail to: salesaddresses@nxp.com

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